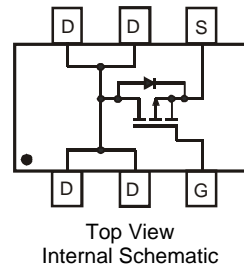


Features

- Low $R_{DS(ON)}$:
 - 40 m Ω @ $V_{GS} = -4.5V$
 - 70 m Ω @ $V_{GS} = -2.5V$
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT26
- Case Material – Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

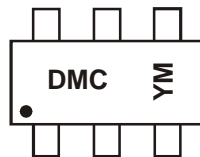


Ordering Information (Note 3)

Part Number	Case	Packaging
DMP2066LDM-7	SOT26	3000/Tape & Reel
DMP2066LDMQ-7	SOT26	3000/Tape & Reel

- Notes:
1. No purposefully added lead.
 2. Diodes Inc's "Green" policy can be found on our website at <http://www.diodes.com>.
 3. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



DMC = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: V = 2008)
 M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±12	V
Drain Current (Note 4) Continuous	I _D	-4.6 -3.7	A
		T _A = 25°C T _A = 70°C	
Pulsed Drain Current (Note 5)	I _{DM}	-18	A
Body-Diode Continuous Current (Note 4)	I _S	2.0	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 4)	P _D	1.25	W
Thermal Resistance, Junction to Ambient (Note 4); Steady-State	R _{θJA}	100	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	I _D = -250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Body Leakage Current	I _{GSS}	—	—	±100	nA	V _{DS} = 0V, V _{GS} = ±12V
Gate Threshold Voltage	V _{GS(th)}	-0.6	-0.96	-1.2	V	V _{DS} = V _{GS} , I _D = -250μA
On State Drain Current (Note 6)	I _{D(ON)}	-15	—	—	A	V _{GS} = -4.5V, V _{DS} = -5V
Static Drain-Source On-Resistance (Note 6)	R _{DS(ON)}	—	29 55	40 70	mΩ	V _{GS} = -4.5V, I _D = -4.6A V _{GS} = -2.5V, I _D = -3.8A
Forward Transconductance (Note 6)	g _{FS}	—	9	—	S	V _{DS} = -10V, I _D = -4.6A
Diode Forward Voltage (Note 6)	V _{SD}	-0.5	-0.72	-1.4	V	I _S = -2.1A, V _{GS} = 0V
Maximum Body-Diode Continuous Current (Note 4)	I _S	—	—	1.7	A	—
DYNAMIC PARAMETERS (Note 7)						
Input Capacitance	C _{iss}	—	820	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	200	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	160	—	pF	
Gate Resistance	R _G	—	2.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V f = 1.0MHz
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q _G	—	10.1	—	nC	V _{DS} = -10V, V _{GS} = -4.5V, I _D = -4.5A
Gate-Source Charge	Q _{GS}	—	1.5	—		
Gate-Drain Charge	Q _{GD}	—	4.3	—		
Turn-On Delay Time	t _{d(on)}	—	4.4	—	ns	V _{DS} = -10V, V _{GS} = -4.5V, I _D = -1A, R _G = 6.0Ω
Rise Time	t _r	—	9.9	—		
Turn-Off Delay Time	t _{d(off)}	—	28.0	—		
Fall Time	t _f	—	23.4	—		

- Notes:
- Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t ≤ 10s.
 - Repetitive Rating, pulse width limited by junction temperature.
 - Test pulse width t = 300μs.
 - Guaranteed by design. Not subject to production testing.

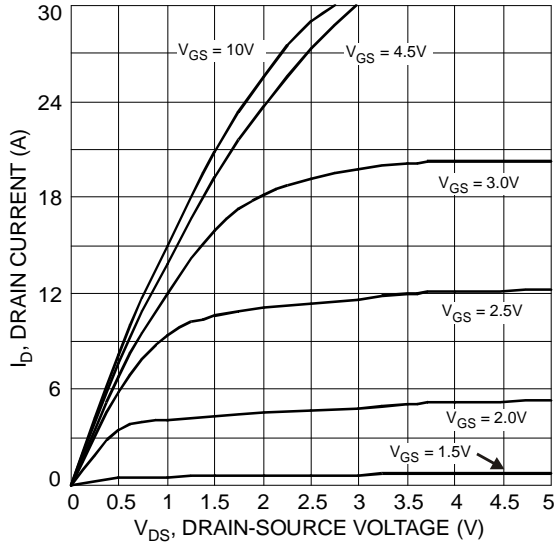


Fig. 1 Typical Output Characteristic

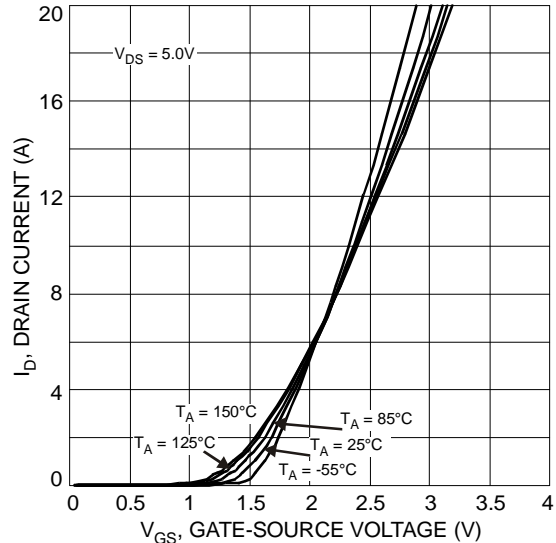


Fig. 2 Typical Transfer Characteristic

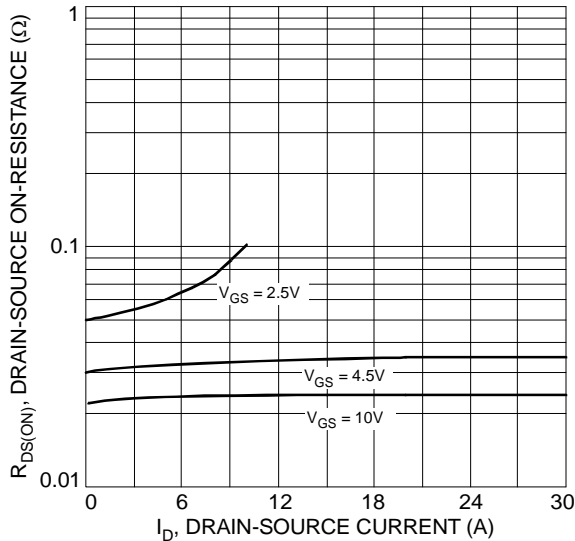


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

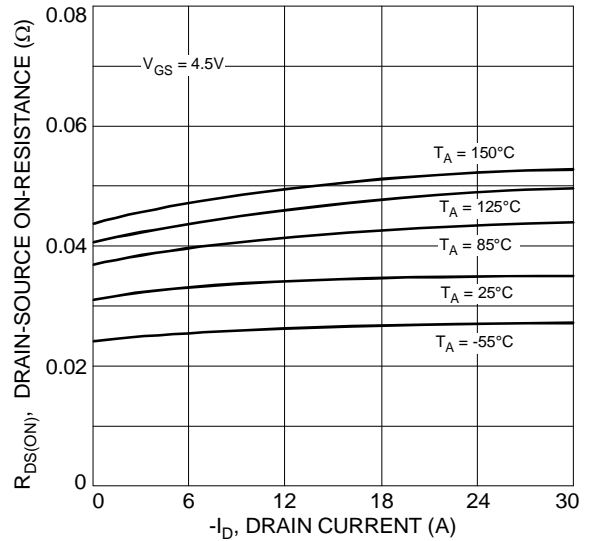


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

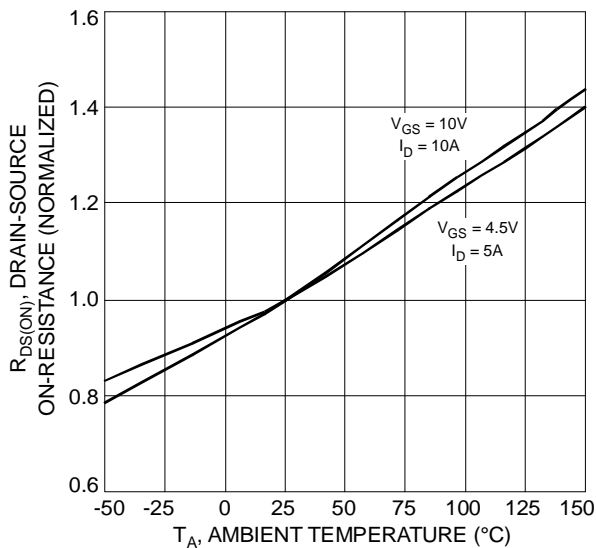


Fig. 5 Normalized On-Resistance vs. Ambient Temperature

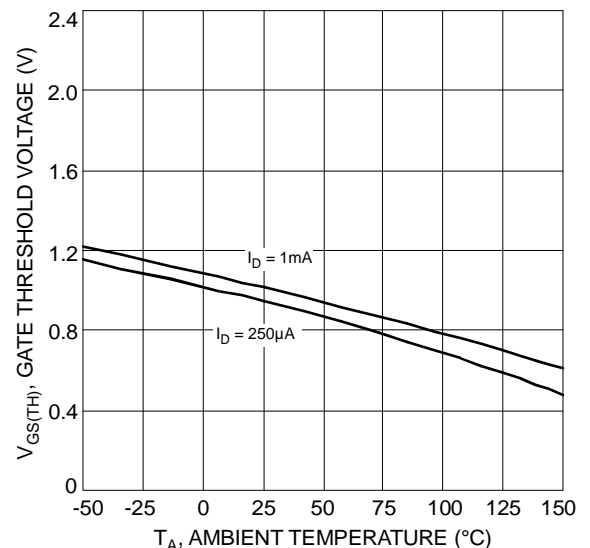


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

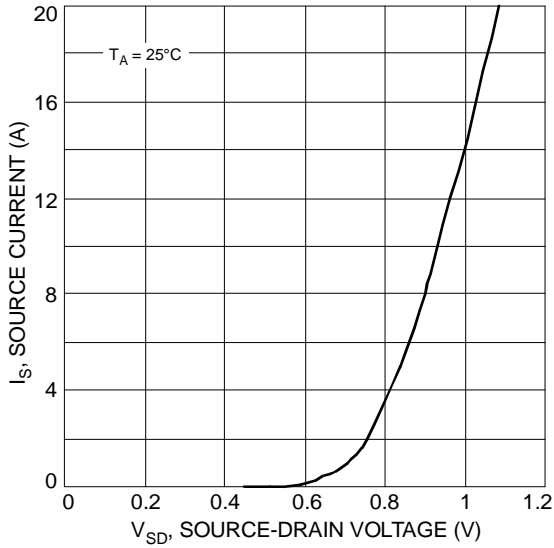


Fig. 7 Diode Forward Voltage vs. Current

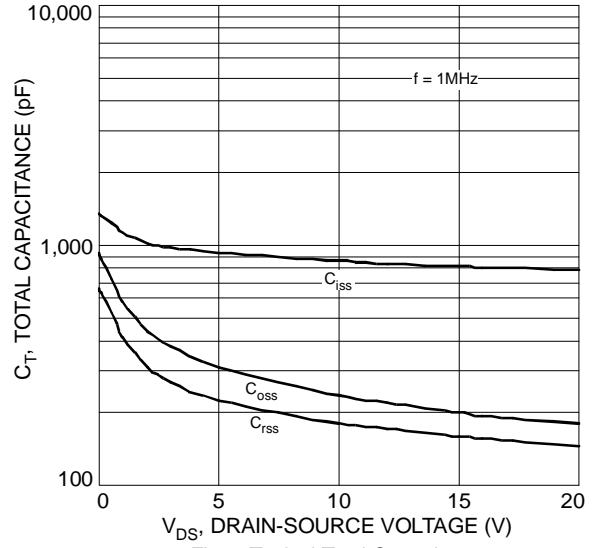


Fig. 8 Typical Total Capacitance

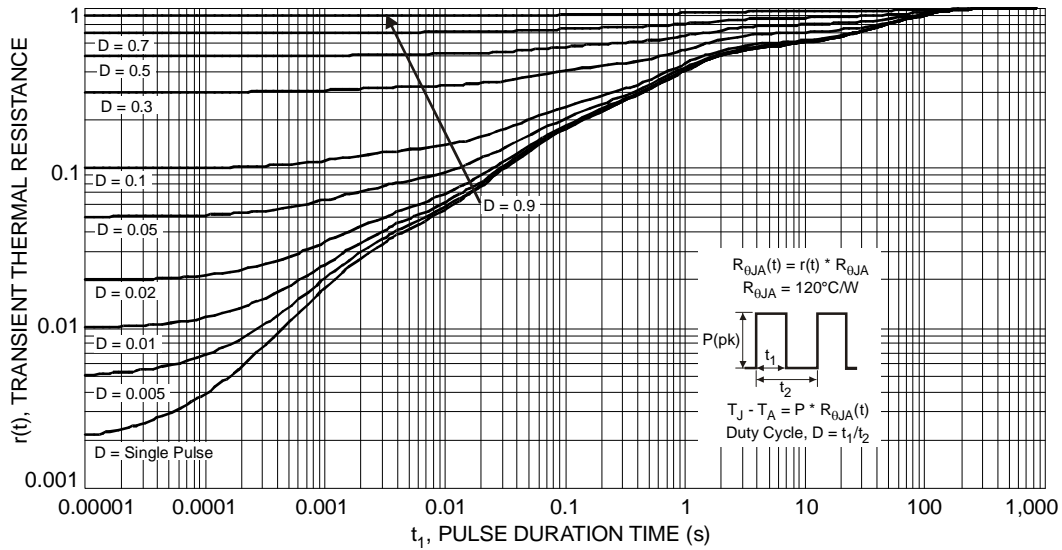
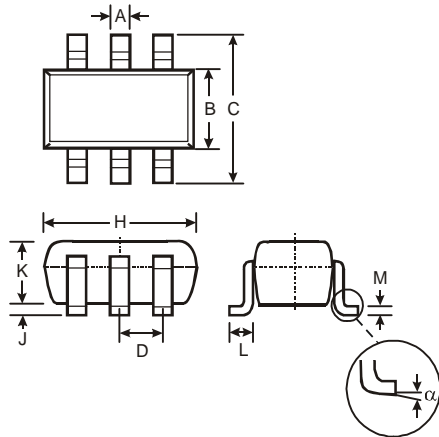


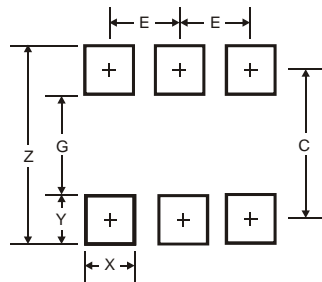
Fig. 9 Transient Thermal Response

Package Outline Dimensions



SOT26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C	2.40
E	0.95

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